NSN 5962-01-293-4112

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-293-4112

Body Length: 0.960 inches **Body Width:** Between 0.220 inches and 0.310 inches **Body Height:** Between 0.140 inches and 0.185 inches **Maximum Power Dissipation Rating:** 794.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **Features Provided:** Hermetically sealed and burn in and bipolar and programmable and 3-state output **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 12 input **Case Outline Source And Designator:** D-6 mil-m-38510 **Terminal Surface Treatment:** Solder Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source **Time Rating Per Chacteristic:** 85.00 nanoseconds propagation delay time, low to high level output and 85.00 nanoseconds propagation delay time, high to low level output Memory Device Type: Prom **Memory Capacity:** Unknown **Test Data Document:** 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). **Terminal Type And Quantity:** 18 printed circuit Shelf Life: N/a Unit Of Measure:

NSN 5962-01-293-4112

Memory Microcircuit - Page 2 of 2

Demilitarization:

No

Fiig:

A458a0

